## Electronic supporting Information

## Interfacial Anion Vacancies Engineered Graphitic Carbon Nitride Photoelectrode for Promoting Charge Separation

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Figure S1. Top viewed (a) and cross-sectional SEM images (b) of ZnO nanorod.



Figure S2. EDS results of ZnO@ZnSe in Figure 2(a). The EDS images recorded on a scale of 10  $\mu$ m.



**Figure S3.** EDS of ZnO@ZnSe@g-C<sub>3</sub>N<sub>4</sub> in Figure 2(b). The EDS images recorded on a scale of 10  $\mu$ m.



Figure S4. XRD result of FTO (green), ZnO (black), ZnO@ZnSe (blue) and ZnO@ZnSe@g-C<sub>3</sub>N<sub>4</sub> (red).



Figure S5. XPS spectra of wide range (a) and binding energy of Zn (b) in ZnO (black), ZnO@ZnSe (blue) and ZnO@ZnSe@g-C<sub>3</sub>N<sub>4</sub> (red).



**Figure S6.** LSV of ZnO (black), ZnO@ZnSe (blue) and ZnO@ZnSe@g-C<sub>3</sub>N<sub>4</sub> (red) under dark (empty mark) and under illumination (filled mark).



Figure S7. LSV of ZnO@ZnSe@g-C<sub>3</sub>N<sub>4</sub> in N<sub>2</sub> treatment (red) and in air treatment (black).



**Figure S8.** Band diagram of ZnO, ZnSe and  $g-C_3N_4$  of Figure 8(b).